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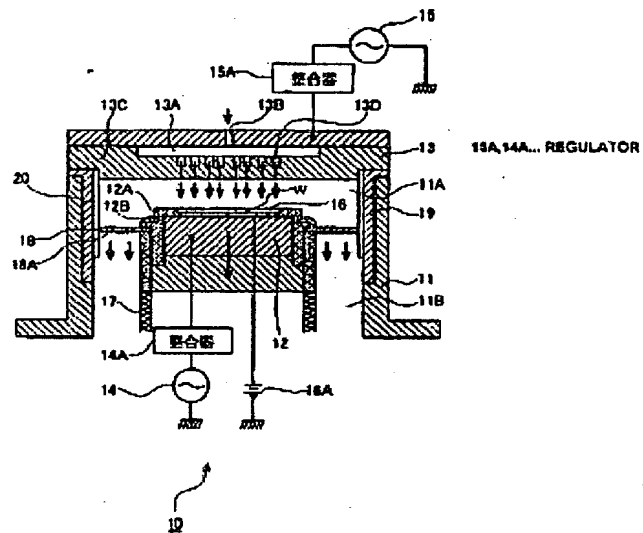
Cited documents:

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Abstract of WO0239495

A plasma processing device, comprising a lower electrode (12) for supporting a wafer (W) inside a chamber (11), a shielding member (19) for shielding the inner peripheral surface of the chamber (11) from the plasma for processing the wafer (W), and a baffle plate (18) disposed in a space between the shielding member (19) and the lower electrode (12) and dispersedly discharging the gas inside the chamber (11), wherein a resin plate (20) is replaceably installed on the inner peripheral surface of the shielding member (19), and a compressive pressure in circumferential direction is provided to the resin plate (20).



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